

$V_{RRM}$	=	5500 V
$I_{F(AV)M}$	=	175 A
$I_{FSM}$	=	$3 \times 10^3$ A
$V_{(T0)}$	=	3.35 V
$r_T$	=	7.2 mW
$V_{DC-link}$	=	3300 V

# Fast Recovery Diode

## 5SDF 02D6004

### PRELIMINARY

Doc. No. 5SYA1118-02 Okt. 02

- Patented free-floating technology
- Industry standard housing
- Cosmic radiation withstand rating
- Low on-state and switching losses
- Optimized for snubberless operation

## Blocking

### Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	$f = 50$ Hz, $t_p = 10$ ms, $T_{vj} = 115^\circ\text{C}$	5500	V
Permanent DC voltage for 100 FIT failure rate	$V_{DC-link}$	Ambient cosmic radiation at sea level in open air. (100% Duty)	3300	V
Permanent DC voltage for 100 FIT failure rate	$V_{DC-link}$	Ambient cosmic radiation at sea level in open air. (5% Duty)	3900	V

### Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Repetitive peak reverse current	$I_{RRM}$	$V_R = V_{RRM}$ , $T_{vj} = 115^\circ\text{C}$			20	mA

## Mechanical data

### Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Mounting force	$F_m$		14	16	18	kN
Acceleration	$a$	Device unclamped			50	$\text{m/s}^2$
Acceleration	$a$	Device clamped			200	$\text{m/s}^2$

### Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Weight	$m$				0.25	kg
Housing thickness	$H$		26.0		26.6	mm
Surface creepage distance	$D_s$		30			mm
Air strike distance	$D_a$		20			mm

Note 1 Maximum rated values indicate limits beyond which damage to the device may occur

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## On-state

### Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Max. average on-state current	$I_{F(AV)M}$	Half sine wave, $T_C = 70\text{ °C}$			175	A
Max. RMS on-state current	$I_{F(RMS)}$				275	A
Max. peak non-repetitive surge current	$I_{FSM}$	$t_p = 10\text{ ms}$ , $T_{vj} = 115\text{ °C}$ , $V_R = 0\text{ V}$			$3 \times 10^3$	A
Limiting load integral	$I^2t$				$45 \times 10^3$	A <sup>2</sup> s
Max. peak non-repetitive surge current	$I_{FSM}$	$t_p = 1\text{ ms}$ , $T_{vj} = 115\text{ °C}$ , $V_R = 0\text{ V}$			$8 \times 10^3$	A
Limiting load integral	$I^2t$				$32 \times 10^3$	A <sup>2</sup> s

### Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
On-state voltage	$V_F$	$I_F = 520\text{ A}$ , $T_{vj} = 115\text{ °C}$			7.1	V
Threshold voltage	$V_{(T0)}$	$T_{vj} = 115\text{ °C}$			3.35	V
Slope resistance	$r_T$	$I_F = 200 \dots 1000\text{ A}$			7.2	mΩ

## Turn-on

### Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Peak forward recovery voltage	$V_{FRM}$	$di/dt = 1000\text{ A}/\mu\text{s}$ , $T_{vj} = 115\text{ °C}$			370	V

## Turn-off

### Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Max. decay rate of on-state current	$di/dt_{crit}$	$I_{FM} = \text{A}$ , $T_{vj} = 115\text{ °C}$ $V_{DC-link} = 3300\text{ V}$			220	A/μs

### Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Reverse recovery current	$I_{RM}$	$I_{FQ} = 520\text{ A}$ , $V_{DC-Link} = 3300\text{ V}$			300	A
Reverse recovery charge	$Q_{rr}$	$di/dt = 220\text{ A}/\mu\text{s}$ , $L_{CL} = \text{nH}$				μC
Turn-off energy	$E_{rr}$	$C_{CL} = \mu\text{F}$ , $R_{CL} = \Omega$ , $T_j = 115\text{ °C}$			1.8	J

## Thermal

### Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Operating junction temperature range	$T_{vj}$		-40		115	°C
Storage temperature range	$T_{stg}$		-40		125	°C

### Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Thermal resistance junction to case	$R_{th(j-c)}$	Double-side cooled $F_m = 14...18$ kN			40	K/kW
	$R_{th(j-c)A}$	Anode-side cooled $F_m = 14...18$ kN			80	K/kW
	$R_{th(j-c)C}$	Cathode-side cooled $F_m = 14...18$ kN			80	K/kW
Thermal resistance case to heatsink	$R_{th(c-h)}$	Double-side cooled $F_m = 14...18$ kN			8	K/kW
	$R_{th(c-h)}$	Single-side cooled $F_m = 14...18$ kN			16	K/kW

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_{th i} (1 - e^{-t/t_i})$$

i	1	2	3	4
$R_{th i}$ (K/kW)	25.699	9.472	3.381	1.466
$\tau_i$ (s)	0.3802	0.0483	0.0060	0.0018

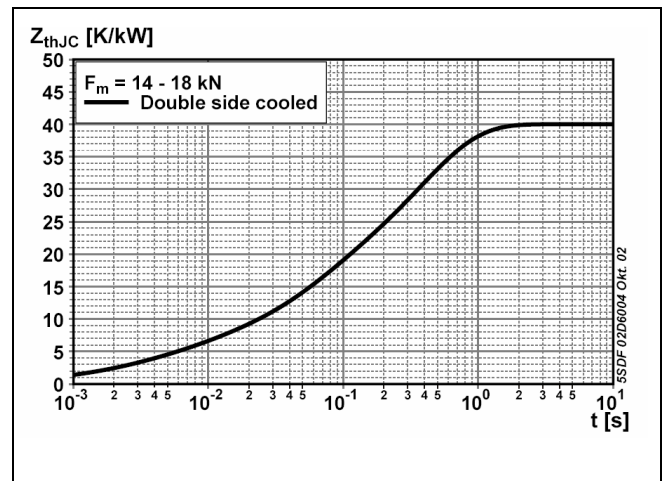


Fig. 1 Transient thermal impedance (junction to case) vs. time in analytical and graphical form (max. values)

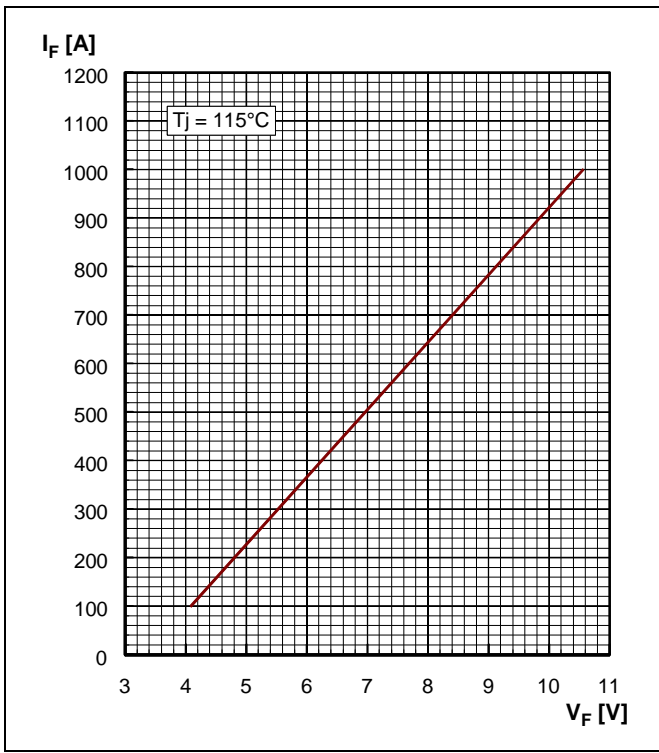


Fig. 2 Forward current vs. forward voltage

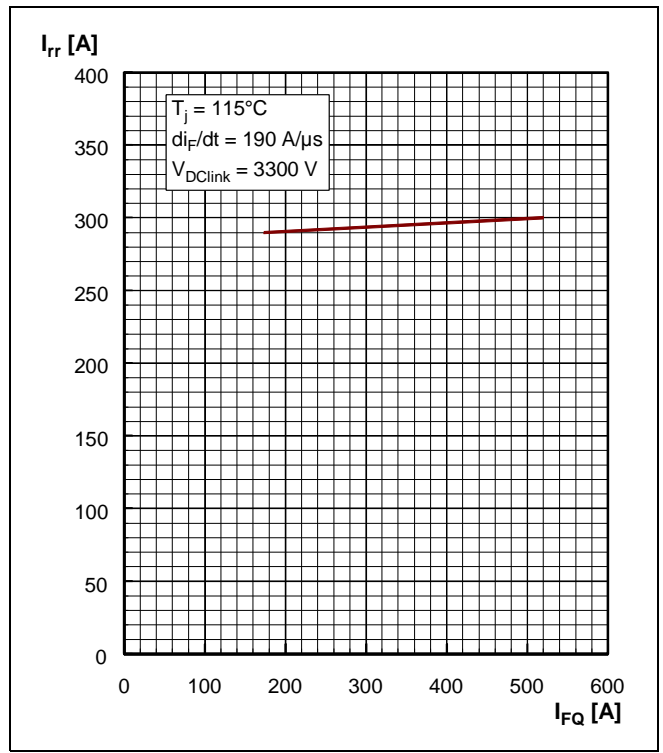


Fig. 3 Diode reverse recovery current vs. turn-off current

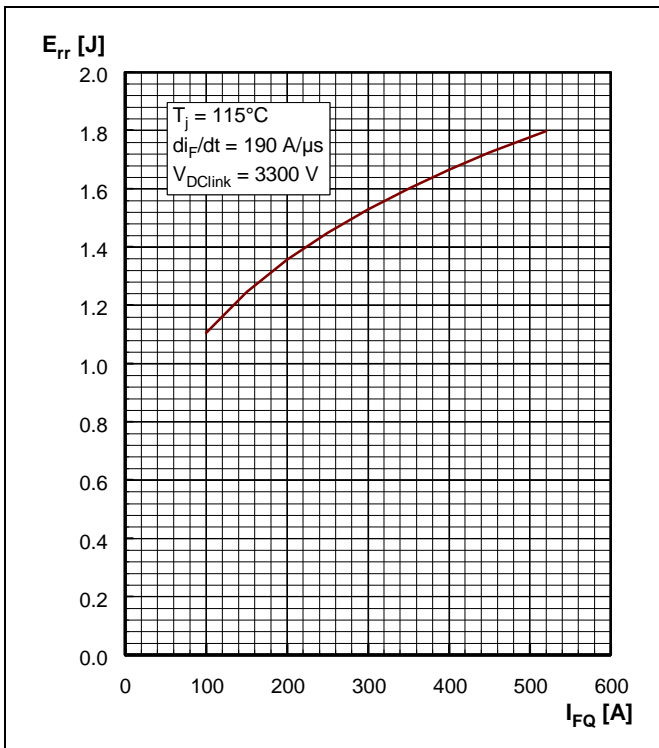


Fig. 4 Diode turn-off energy per pulse vs. turn-off current

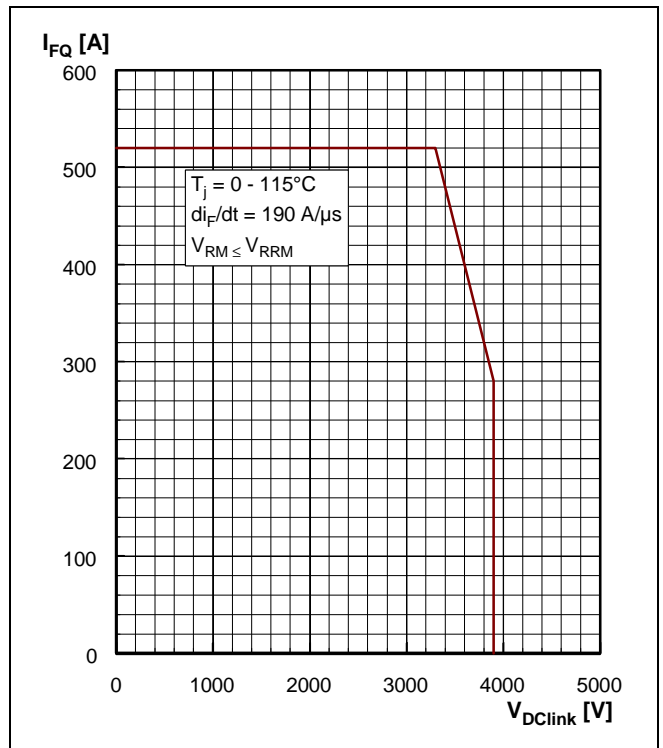


Fig. 5 Max. repetitive diode forward current

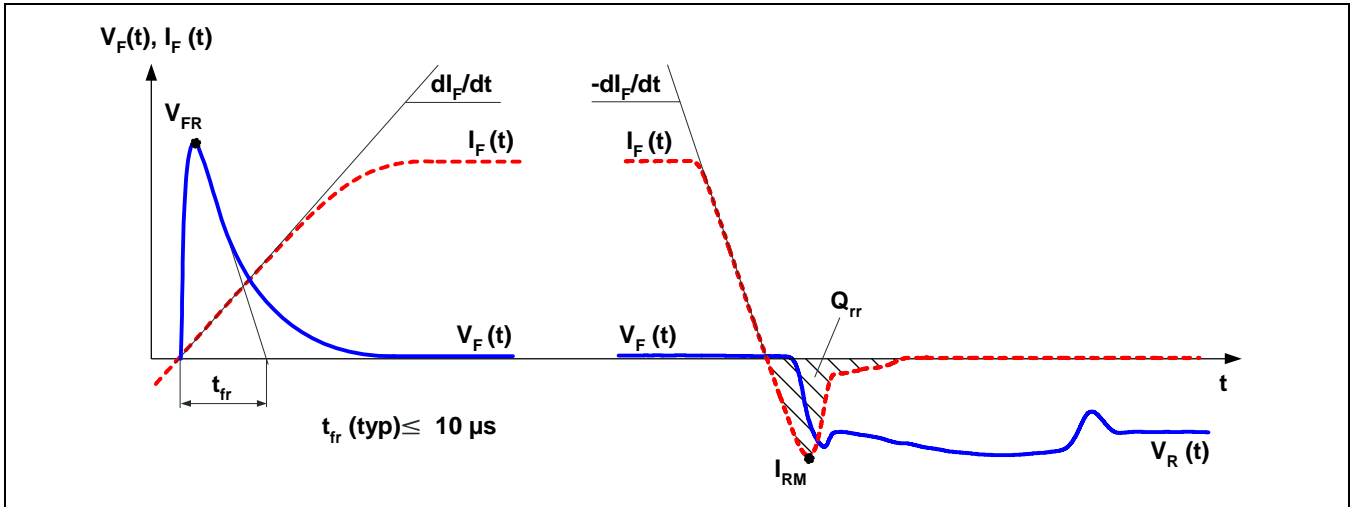


Fig. 6 General current and voltage waveforms

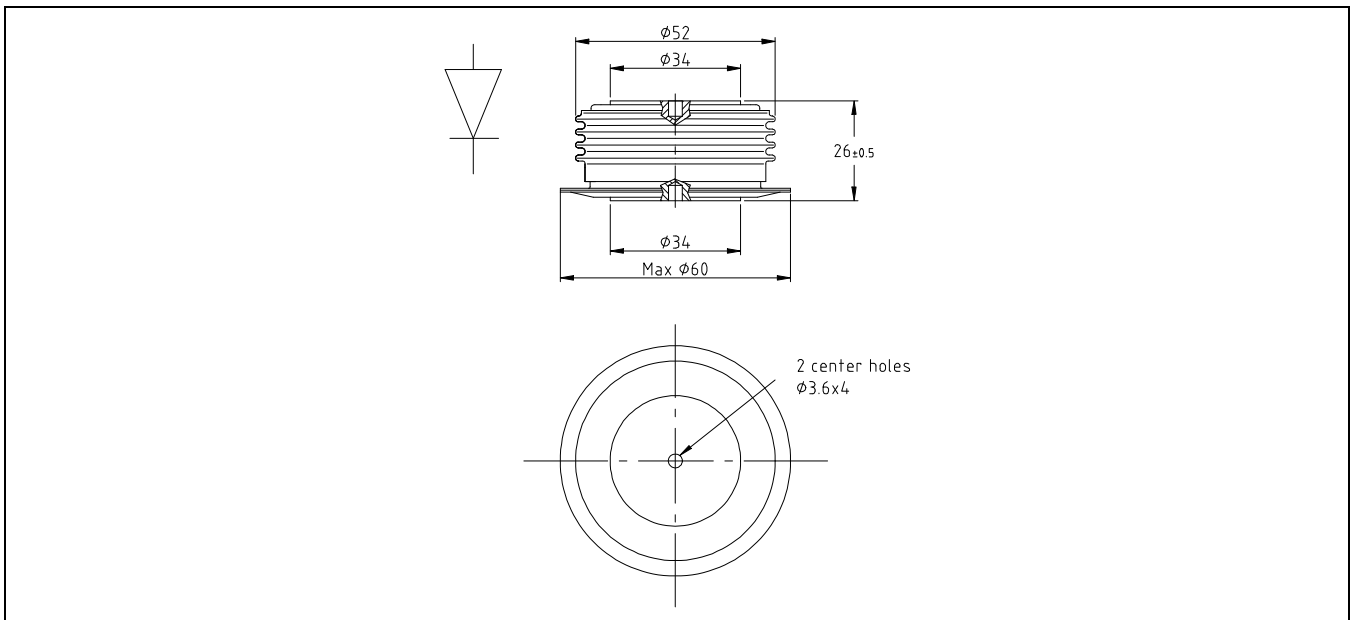


Fig. 7 Outline drawing; all dimensions are in millimeters and represent nominal values unless stated otherwise

### Related documents:

Doc. Nr	Titel
5SYA 2036	Recommendations regarding mechanical clamping of Press Pack High Power Semiconductors
5SZK 9104	Specification of environmental class for pressure contact diodes, PCTs and GTO, STORAGE available on request, please contact factory
5SZK 9105	Specification of environmental class for pressure contact diodes, PCTs and GTO, TRANSPORTATION available on request, please contact factory

Please refer to <http://www.abb.com/semiconductors> for current version of documents.

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